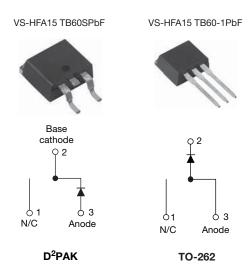




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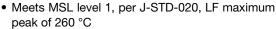
# HEXFRED®, Ultrafast Soft Recovery Diode, 15 A



PRODUCT SUMMARY						
Package	TO-263AB (D <sup>2</sup> PAK), TO-262AA					
I <sub>F(AV)</sub>	15 A					
$V_{R}$	600 V					
V <sub>F</sub> at I <sub>F</sub>	1.7 V					
t <sub>rr</sub> (typ.)	23 ns					
T <sub>J</sub> max.	150 °C					
Diode variation	Single die					

#### **FEATURES**

- · Ultrafast and ultrasoft recovery
- Very low I<sub>RRM</sub> and Q<sub>rr</sub>





HALOGEN

FREE

- Halogen-free according to IEC61249-2-21 definition
- Compliant to RoHS Directive 2002/95/EC
- · Designed and qualified for industrial level
- AEC-Q101 qualified

#### **BENEFITS**

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

#### **DESCRIPTION**

VS-HFA15TB60SPbF, VS-HFA15TB60-1PbF is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 15 A continuous current, the VS-HFA15TB60SPbF, VS-HFA15TB60-1PbF is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (IRRM) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA15TB60SPbF, VS-HFA15TB60-1PbF is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Cathode to anode voltage	$V_R$		600	V			
Maximum continuous forward current	I <sub>F</sub>	T <sub>C</sub> = 100 °C	15				
Single pulse forward current	I <sub>FSM</sub>		150	Α			
Maximum repetitive forward current	I <sub>FRM</sub>		60				
Maximum nawar discination	P <sub>D</sub>	T <sub>C</sub> = 25 °C	74	W			
Maximum power dissipation		T <sub>C</sub> = 100 °C	29	] vv			
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 55 to + 150	°C			



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<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V <sub>BR</sub>	I <sub>R</sub> = 100 μA		600	-	-	
Maximum forward voltage		I <sub>F</sub> = 15 A		-	1.3	1.7	V
	$V_{FM}$	I <sub>F</sub> = 30 A	See fig. 1	-	1.5	2.0	
		I <sub>F</sub> = 15 A, T <sub>J</sub> = 125 °C		-	1.2	1.6	
Maximum reverse		V <sub>R</sub> = V <sub>R</sub> rated	Coofin 0	-	1.0	10	
leakage current	I <sub>RM</sub>	$T_J = 125  ^{\circ}\text{C},  V_R = 0.8  \text{x}  V_R  \text{rated}$	See fig. 2	-	400	1000	μA
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V See fig. 3		-	25	50	pF
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from p	ackage body	-	8.0	-	nH

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A}$	4/μs, V <sub>R</sub> = 30 V	-	23	-	
Reverse recovery time See fig. 5	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	50	60	ns
	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	105	120	
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 15 A	-	4.5	6.0	Α
See fig. 6	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C		-	6.5	10	
Reverse recovery charge	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C	dl <sub>F</sub> /dt = 200 A/μs	-	84	180	nC
See fig. 7	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C	V <sub>R</sub> = 200 V	-	241	600	iiC
Peak rate of fall of recovery	dI <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	188	-	A/µs
current during t <sub>b</sub> See fig. 8	dI <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	160	-	Ανμδ

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	1.7		
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Typical socket mount	-	-	80	K/W	
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-		
Weight			-	2.0	-	g	
vveignt			-	0.07	-	oz.	
Madisadaisa		Case style D <sup>2</sup> PAK	HFA15TB60S			•	
Marking device		Case style TO-262		HFA15TB60-1			





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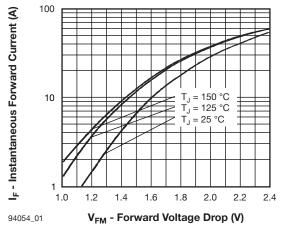


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

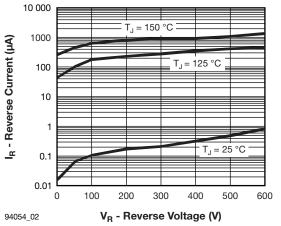


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

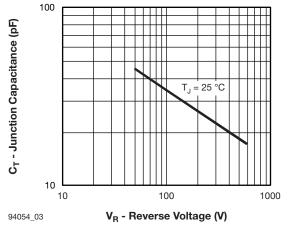


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

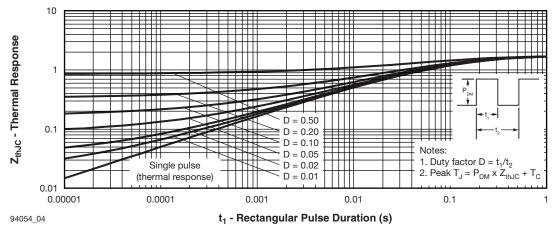


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics



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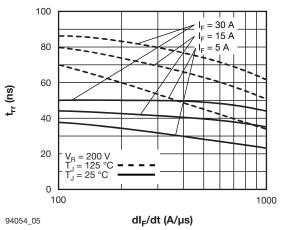


Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

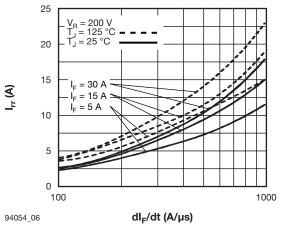


Fig. 6 - Typical Recovery Current vs. dl<sub>F</sub>/dt

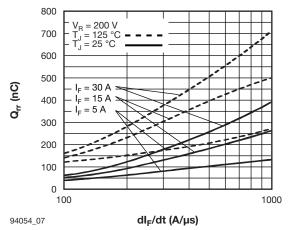


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

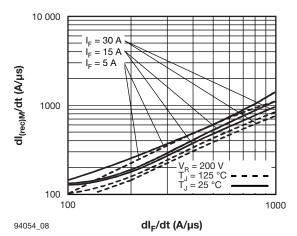


Fig. 8 - Typical dl<sub>(rec)M</sub>/dt vs. dl<sub>F</sub>/dt

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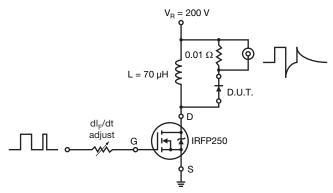
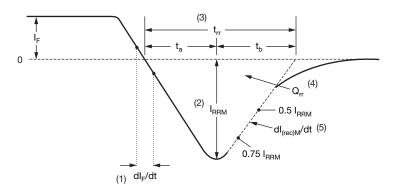


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_{F}$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{rr}$  area under curve defined by  $\mathbf{t}_{rr}$  and  $\mathbf{I}_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

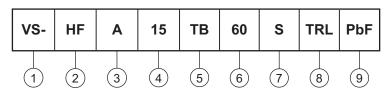
(5) dl<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 10 - Reverse Recovery Waveform and Definitions

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#### **ORDERING INFORMATION TABLE**

#### Device code



- 1 Vishay Semiconductors product
- 2 HEXFRED® family
- 3 Electron irradiated
- 4 Current rating (15 = 15 A)
- 5 Package:
  - TB = TO-220
- 6 Voltage rating (60 = 600 V)
- 7 • S = D<sup>2</sup>PAK
  - • -1 = TO-262
- 8 • None = Tube (50 pieces)
  - TRL = Tape and reel (left oriented, for D2PAK package )
  - TRR = Tape and reel (right oriented, for D<sup>2</sup>PAK package)
- 9 PbF = Lead (Pb)-free
  - P = Lead (Pb)-free (for D<sup>2</sup>PAK TRL and TRR)

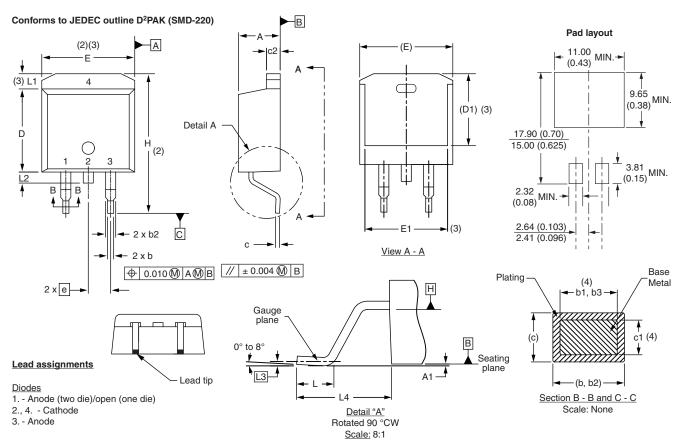
LINKS TO RELATED DOCUMENTS						
Dimensions	TO-263AB (D <sup>2</sup> PAK): www.vishay.com/doc?95046					
Differsions	TO-262AA: www.vishay.com/doc?95419					
Part marking information	TO-263AB (D <sup>2</sup> PAK): www.vishay.com/doc?95054					
Fart marking information	TO-262AA: www.vishay.com/doc?95420					
Packaging information	www.vishay.com/doc?95032					
SPICE model	www.vishay.com/doc?95357					



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## D<sup>2</sup>PAK

#### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIN	LLIMETERS INCHES NOTE		MILLIMETERS		INCHES	
STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES		
Α	4.06	4.83	0.160	0.190			
A1	0.00	0.254	0.000	0.010			
b	0.51	0.99	0.020	0.039			
b1	0.51	0.89	0.020	0.035	4		
b2	1.14	1.78	0.045	0.070			
b3	1.14	1.73	0.045	0.068	4		
С	0.38	0.74	0.015	0.029			
c1	0.38	0.58	0.015	0.023	4		
c2	1.14	1.65	0.045	0.065			
D	8.51	9.65	0.335	0.380	2		

SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STIMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
Е	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54	2.54 BSC		0.100 BSC	
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25	BSC	0.010 BSC		
L4	4.78	5.28	0.188	0.208	

#### Notes

- $^{(1)}$  Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC outline TO-263AB

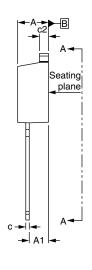


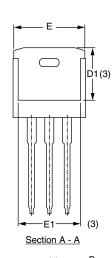
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### **TO-262**

#### **DIMENSIONS** in millimeters and inches

# 



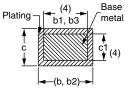


**⊕** 0.010**⋒**|A**⋒**|B

Lead assignments



<u>Diodes</u>
1. - Anode (two die)/open (one die)
2., 4. - Cathode
3. - Anode



Section B - B and C - C Scale: None

CVMDOL	MILLIMETERS		INC	INCHES		
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
А	4.06	4.83	0.160	0.190		
A1	2.03	3.02	0.080	0.119		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
С	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	
D1	6.86	8.00	0.270	0.315	3	
Е	9.65	10.67	0.380	0.420	2, 3	
E1	7.90	8.80	0.311	0.346	3	
е	2.54 BSC		0.100	BSC		
L	13.46	14.10	0.530	0.555		
L1	=	1.65	-	0.065	3	
L2	3.56	3.71	0.140	0.146		

#### Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- $^{(3)}$  Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum) and D1 (minimum) where dimensions derived the actual package outline





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